

SKCD 47 C 170 I



SEMICELL CAL-DIODE

SKCD 47 C 170 I

$I_F = 55 \text{ A}$

$V_{RRM} = 1700 \text{ V}$

Size: 6,8 mm X 6,8 mm

Package: wafer frame

Features

- 600V, 1200V and 1700V
- low forward voltage drop
- easy paralleling due to a small forward voltage spread
- low temperature dependence
- very soft recovery behavior
- small switching losses
- high ruggedness
- compatible to thick wire bonding
- compatible to all standard solder processes

Typical Applications

- freewheeling diode for IGBT
- optimal at frequencies > 8 kHz

Absolute Maximum Ratings

Symbol	Conditions	Values	Units
V_{RRM}	$T_{vj} = 25^\circ\text{C}, I_R = 0,2 \text{ mA}$	1700	V
$I_{F(AV)}$	$T_h = 80^\circ\text{C}, T_{vjmax} = 150^\circ\text{C}$	40	A
I_{FSM}	$T_{vj} = 25^\circ\text{C}, 10 \text{ ms, half sine wave}$	720	A
	$T_{vjmax} = 150^\circ\text{C}, 10 \text{ ms, half sine wave}$	550	A
T_{vjmax}		+ 150	°C

Electrical Characteristics

Symbol	Conditions	min.	typ.	max.	Units
I^2t	$T_{vjmax}, 10 \text{ ms, half sine wave}$			1500	A^2s
I_R	$T_{vj} = 25^\circ\text{C}, V_{RRM}$			0,2	mA
	$T_{vj} = 125^\circ\text{C}, V_{RRM}$			8	mA
V_F	$T_{vj} = 25^\circ\text{C}, I_F = 55 \text{ A}$		2,05	2,5	V
	$T_{vj} = 125^\circ\text{C}, I_F = 55 \text{ A}$		1,8	2,3	V
$V_{(TO)}$	$T_{vj} = 125^\circ\text{C}$		1,11		V
r_T	$T_{vj} = 125^\circ\text{C}$		1,2		$\text{m}\Omega$

Dynamic Characteristics

Symbol	Conditions	min.	typ.	max.	Units
t_{rr}	$T_{vj} = 25^\circ\text{C}, 50 \text{ A}, 1200 \text{ V}, 800 \text{ A}/\mu\text{s}$				ns
	$T_{vj} = 125^\circ\text{C}, 50 \text{ A}, 1200 \text{ V}, 800 \text{ A}/\mu\text{s}$				ns
Q_{rr}	$T_{vj} = 25^\circ\text{C}, 50 \text{ A}, 1200 \text{ V}, 800 \text{ A}/\mu\text{s}$		6		μC
	$T_{vj} = 125^\circ\text{C}, 50 \text{ A}, 1200 \text{ V}, 800 \text{ A}/\mu\text{s}$		15		μC
I_{rrm}	$T_{vj} = 25^\circ\text{C}, 50 \text{ A}, 1200 \text{ V}, 800 \text{ A}/\mu\text{s}$				A
	$T_{vj} = 125^\circ\text{C}, 50 \text{ A}, 1200 \text{ V}, 800 \text{ A}/\mu\text{s}$			45	A

Thermal Characteristics

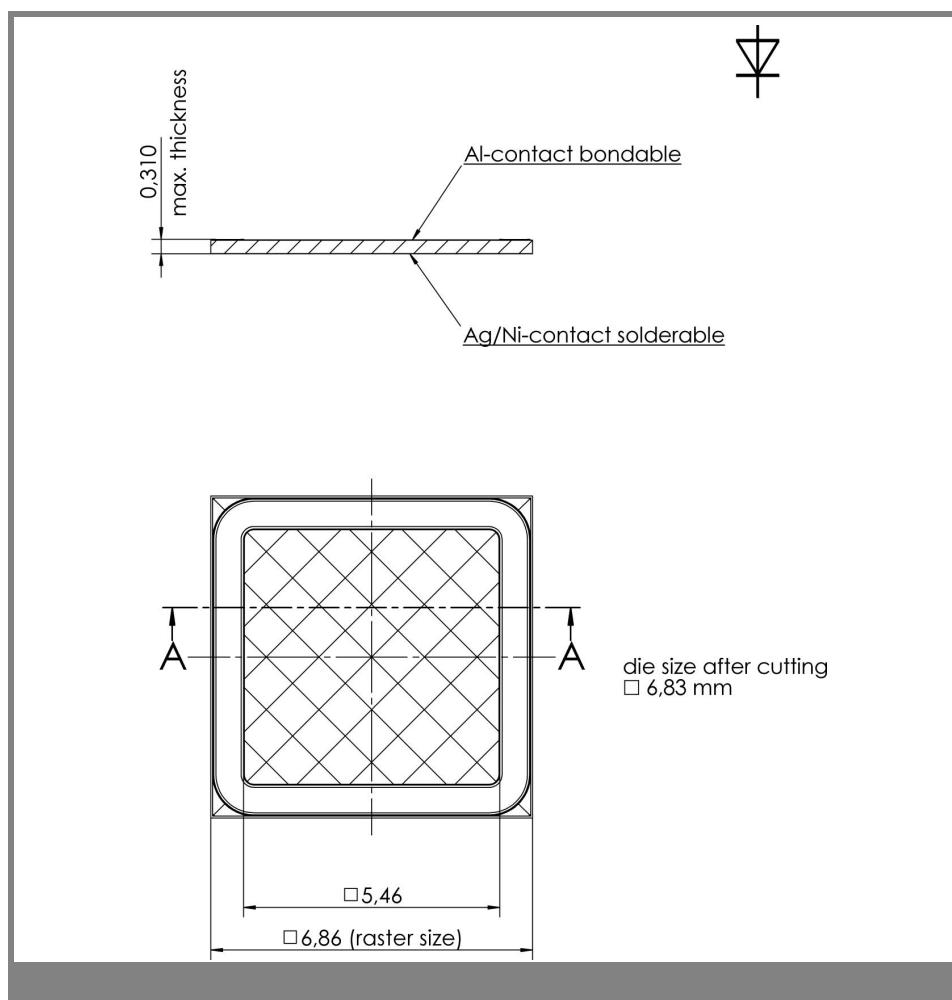
Symbol	Conditions	min.	typ.	max.	Units
T_{vj}		- 40		+ 150	°C
T_{stg}		- 40		+ 150	°C
T_{solder}	10 min			+ 250	°C
T_{solder}	5 min			+ 320	°C
$R_{th(j-h)}$	soldered on 0,38 mm DCB, reference point on copper heatsink close to the chip.		0,7		K / W

Mechanical Characteristics

Parameter	Units
raster size	6,8 x 6,8 mm
Area total	47 mm ²
Chips / wafer	208 pcs
Anode metallisation	bondable (Al)
Cathode metallisation	solderable (Ag / Ni)
wire bond	Al, diameter ≤ 500 µm



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